MOSFET - N-Channel, SOT-23 500 mA, 60 V

Features

- NVBF Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	Vdc
Drain-Gate Voltage	V _{DGS}	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive (t _p ≤ 50 μs)	V _{GS} V _{GSM}	±20 ±40	Vdc Vpk
Drain Current – Continuous – Pulsed	I _D I _{DM}	0.5 0.8	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1.) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



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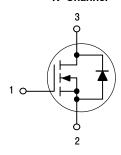
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500 mA, 60 V $R_{DS(on)} = 5 \Omega$

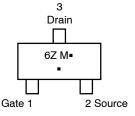


SOT-23 CASE 318 STYLE 21

N-Channel



MARKING DIAGRAM & PIN ASSIGNMENT



6Z = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	3		•		•
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 100 μA)		V _{(BR)DSS}	60	-	Vdc
Gate-Body Leakage Current, Forward (V _{GSF} = 15 Vdc, V _{DS} = 0)		I _{GSS}	_	10	nAdc
ON CHARACTERISTICS	(Note 1)				
Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0$ mA)		V _{GS(th)}	0.8	3.0	Vdc
Static Drain-Source On-Resistance (V _{GS} = 10 Vdc, I _D = 200 mA)		r _{DS(on)}	_	5.0	Ω
On-State Drain Current (V _{DS} = 25 Vdc, V _{GS} = 0)		I _{D(off)}	_	0.5	μΑ
DYNAMIC CHARACTERI	STICS				
Input Capacitance (V _{DS} = 10 Vdc, V _{GS} = 0 V, f = 1.0 MHz)		C _{iss}	-	60	pF
SWITCHING CHARACTE	RISTICS (Note 1)				
Turn-On Delay Time	$(V_{DD} = 25 \text{ Vdc}, I_D = 500 \text{ mA}, R_{qen} = 50 \Omega)$	t _{d(on)}	-	10	ns
Turn-Off Delay Time	Figure 1	t _{d(off)}	-	10	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package Shipping [†]	
MMBF170LT1G	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel
MMBF170LT3G	SOT-23 (TO-236) (Pb-Free)	10000 / Tape & Reel
NVBF170LT1G*	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

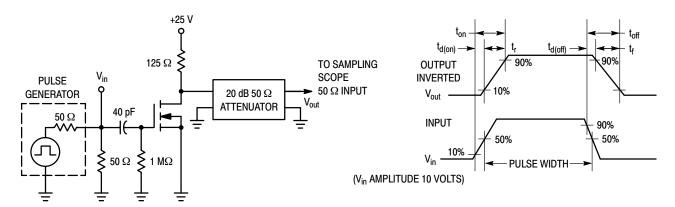


Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

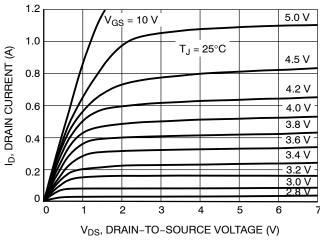


Figure 3. On–Region Characteristics

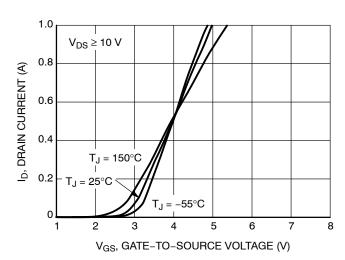


Figure 4. Transfer Characteristics

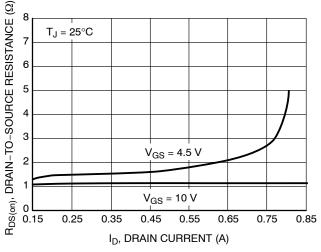


Figure 5. On-Resistance vs. Drain Current and Gate Voltage

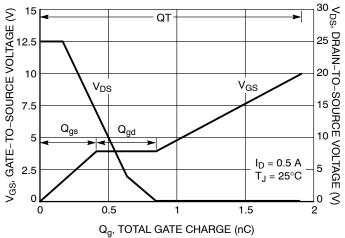


Figure 6. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

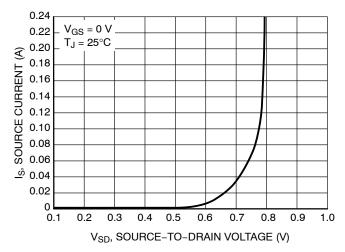


Figure 7. Diode Forward Voltage vs. Current

TYPICAL ELECTRICAL CHARACTERISTICS

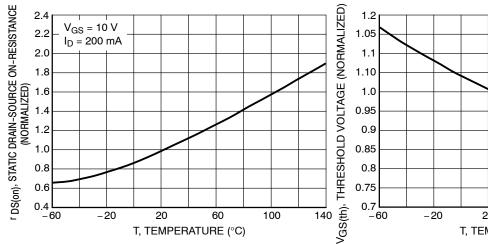


Figure 8. Temperature versus Static Drain-Source On-Resistance

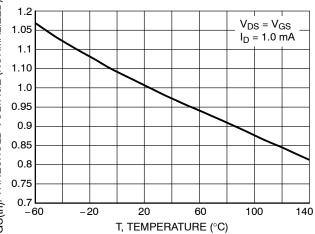


Figure 9. Temperature versus Gate Threshold Voltage

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





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MAX

1.11

0.10

0.50

0.20

3.04

1.40

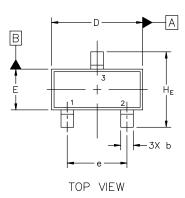
2.04

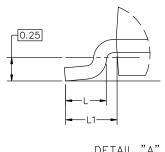
0.55

0.69

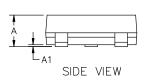
2.64

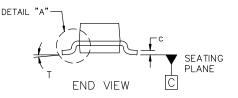
10°

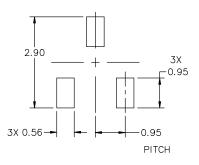




DETAIL "A" Scale 3:1







NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

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DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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